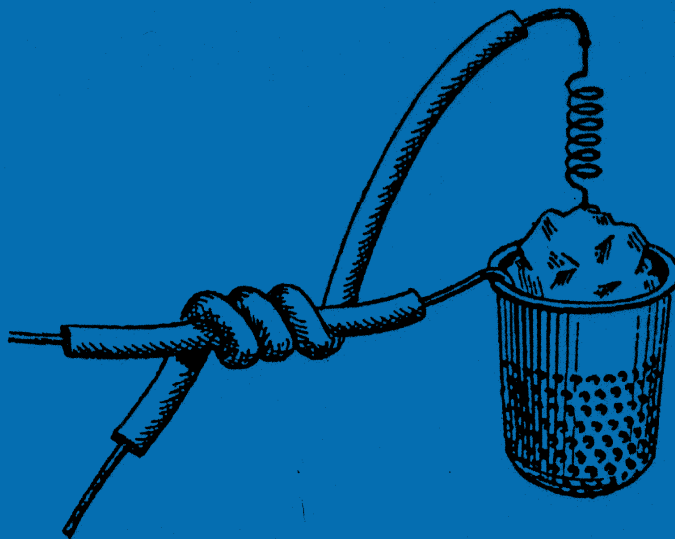
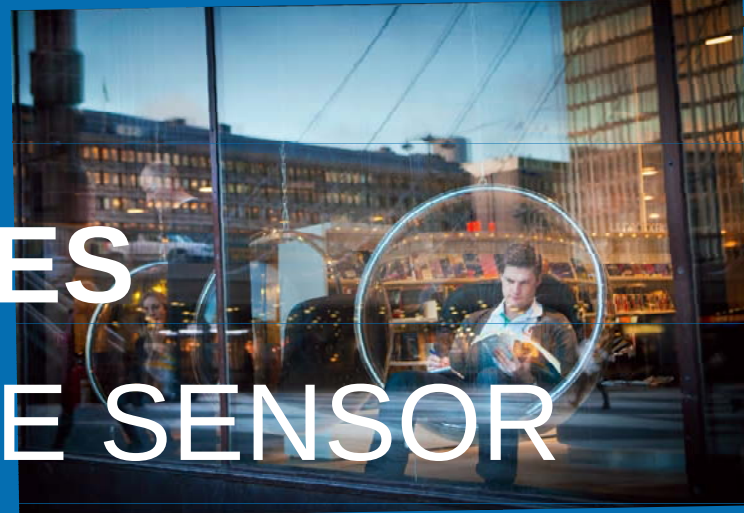


SENSOR DEVICES

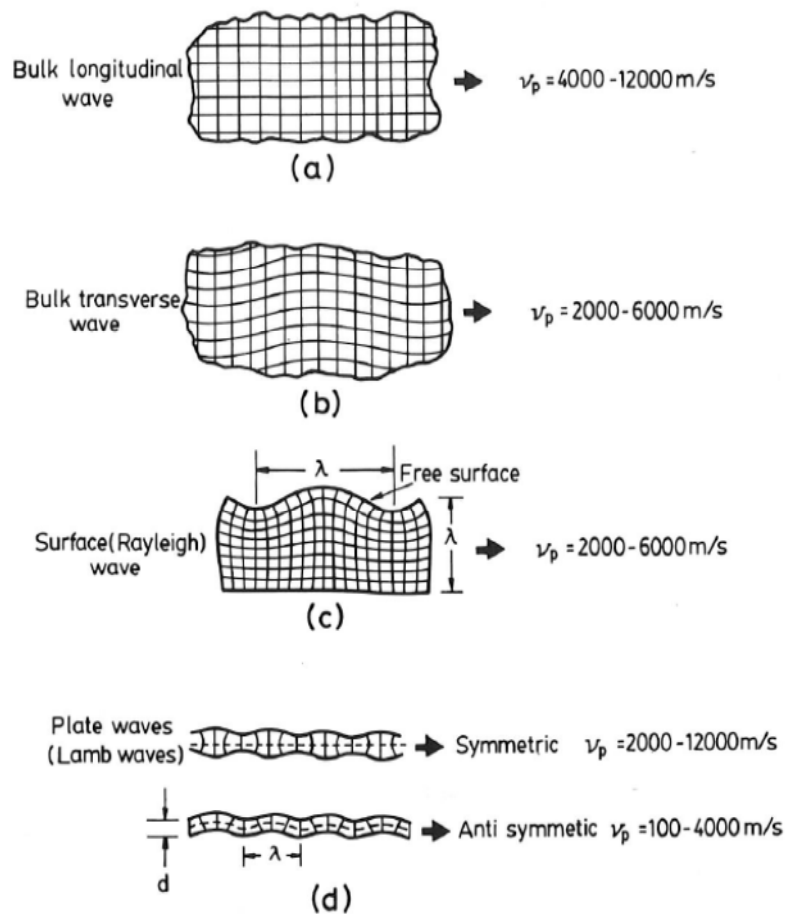
ACOUSTIC WAVE SENSOR



OUTLINE

- **3 Acoustic Wave Sensor**
 - **High sensitivity**
 - **chemical vapour, gas sensing**
- **Oscillation-elastic waves MHz-GHz**
- **Delay time**

ACOUSTIC WAVE SENSORS



Atoms in solid are forced into vibratory motion

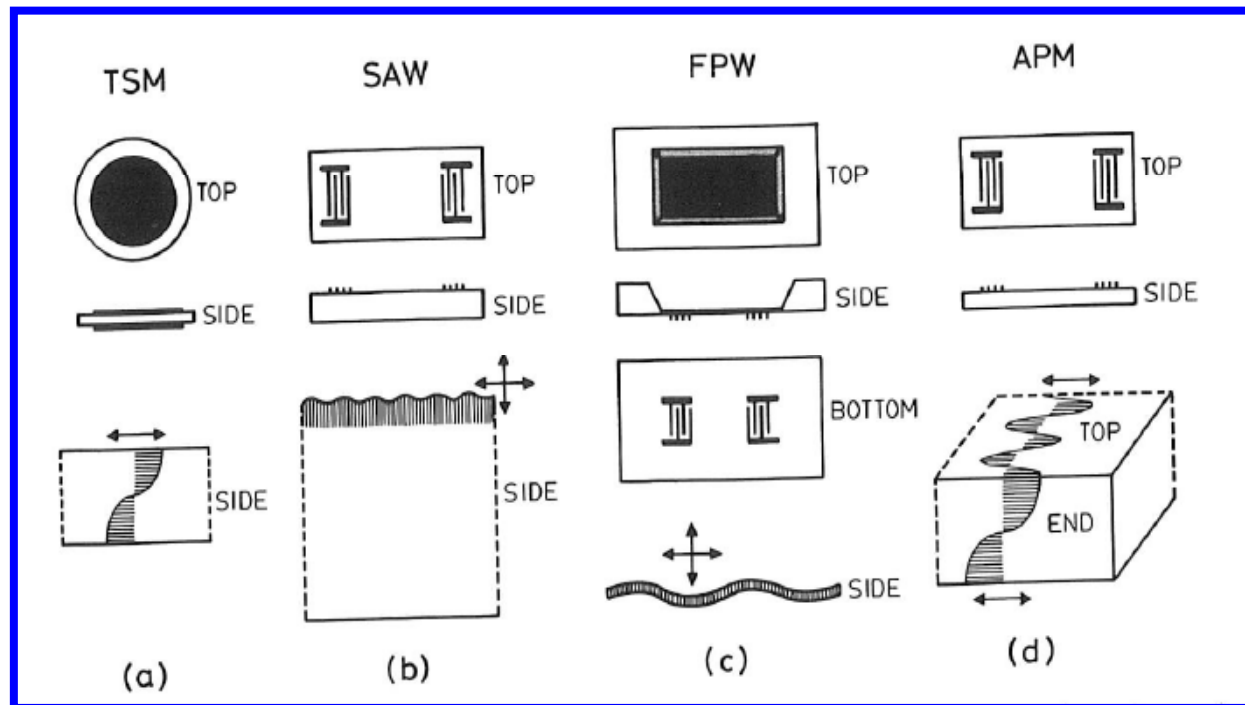
ACOUSTIC WAVE SENSORS

TSM thickness shear mode

SAW surface acoustic wave

FPW flexural plate wave

APM acoustic plate mode



ACOUSTIC WAVE SENSORS

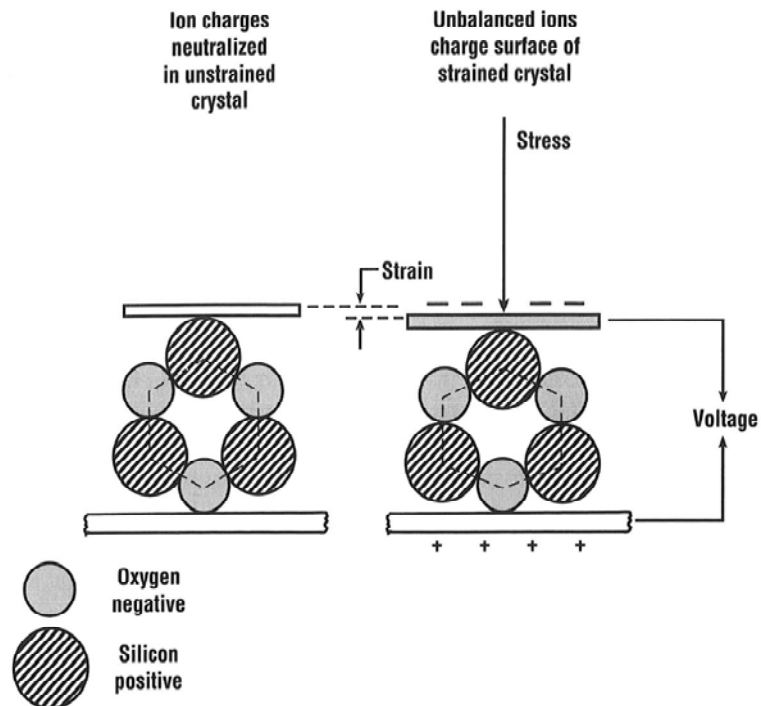


Figure 19.3 Ion position in a piezoelectric crystal lattice such as quartz with and without applied stress (reprinted with permission from Madou [7]. Copyright CRC Press).

How can we get the material to oscillate?

Piezoelectric effect!

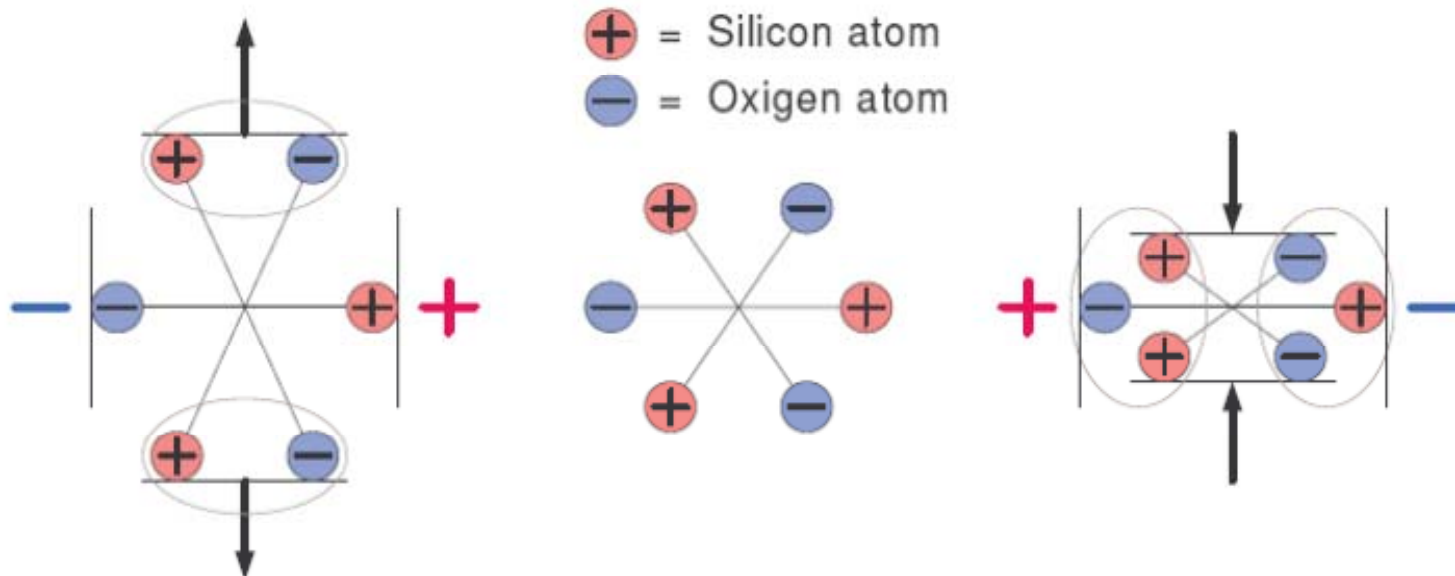
Stress result in voltage

Voltage result in strain

ACOUSTIC WAVE SENSORS

Piezo-electric effect:

- Mechanical strain $\Rightarrow$ voltage
- Voltage $\Rightarrow$ mechanical deformation



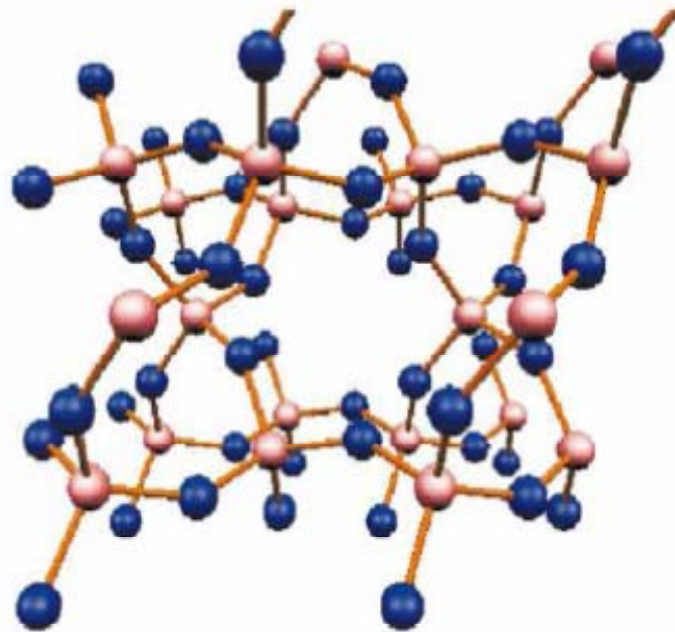
ACOUSTIC WAVE SENSORS

EXAMPLE OF PIEZO MATERIAL

Quartz = SiO_2

Pink = silicon atoms

Blue = oxygen atoms

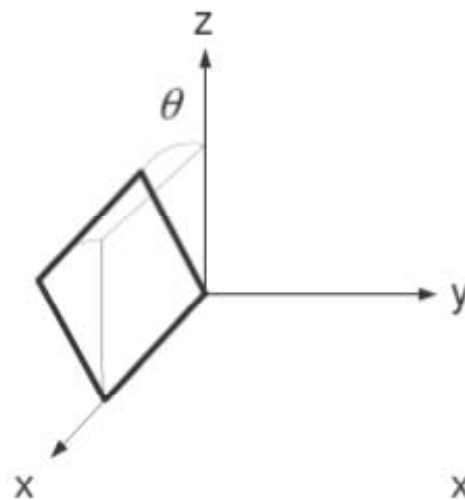
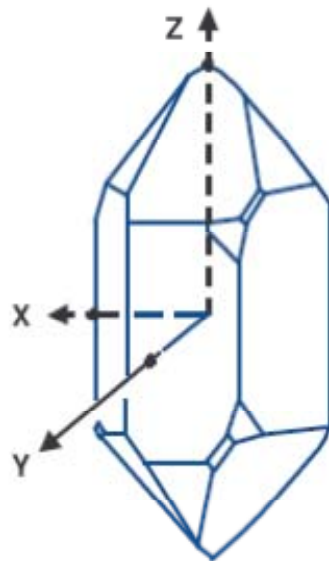


Quartz lattice

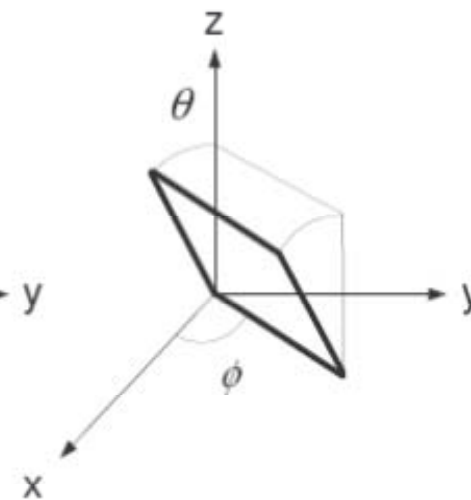
ACOUSTIC WAVE SENSORS

CRYSTAL DIRECTION

Small disks are cut out of the crystal at given angles.



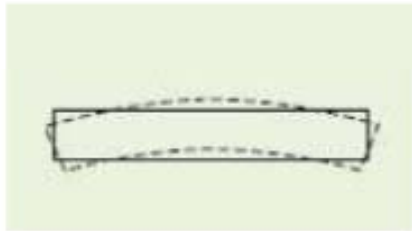
Single rotated cut
(e.g. AT-cut)



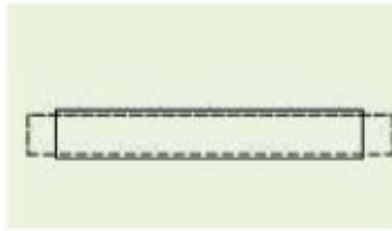
Double rotated cut
(e.g. SC-cut)

ACOUSTIC WAVE SENSORS

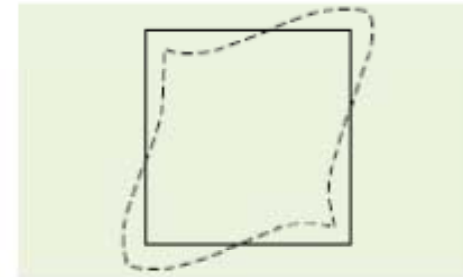
VIBRATION MODES



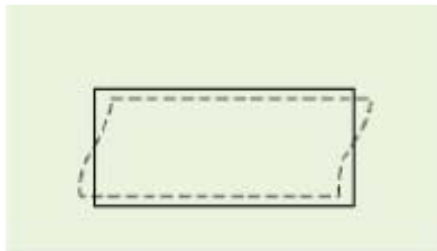
Flexure Mode



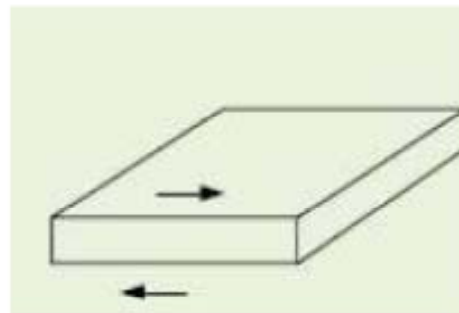
Extensional Mode



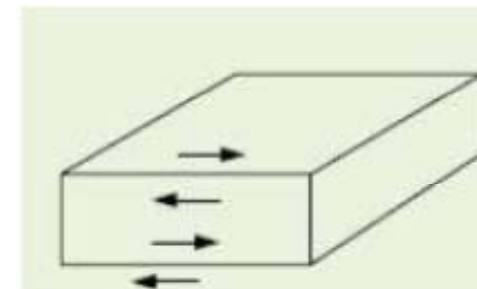
Face Shear Mode



Thickness Shear
Mode

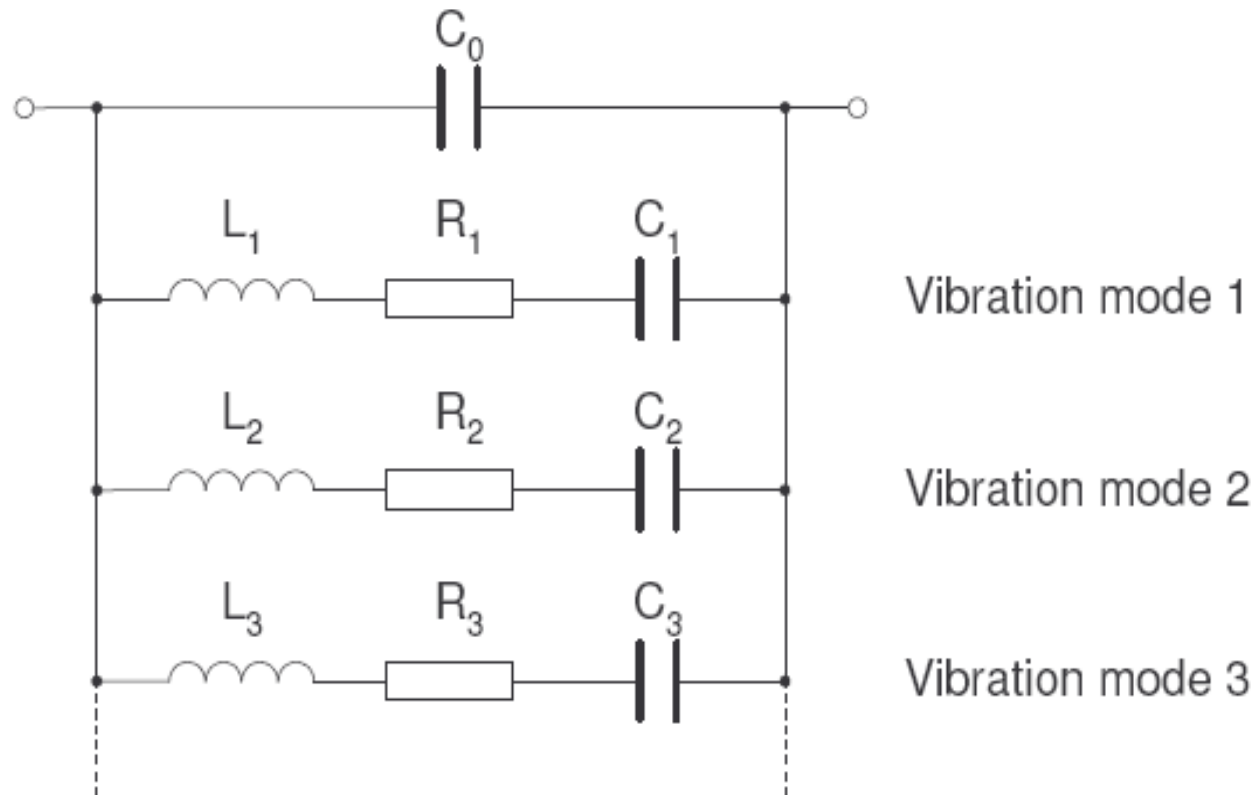


Fundamental Mode
Thickness Shear

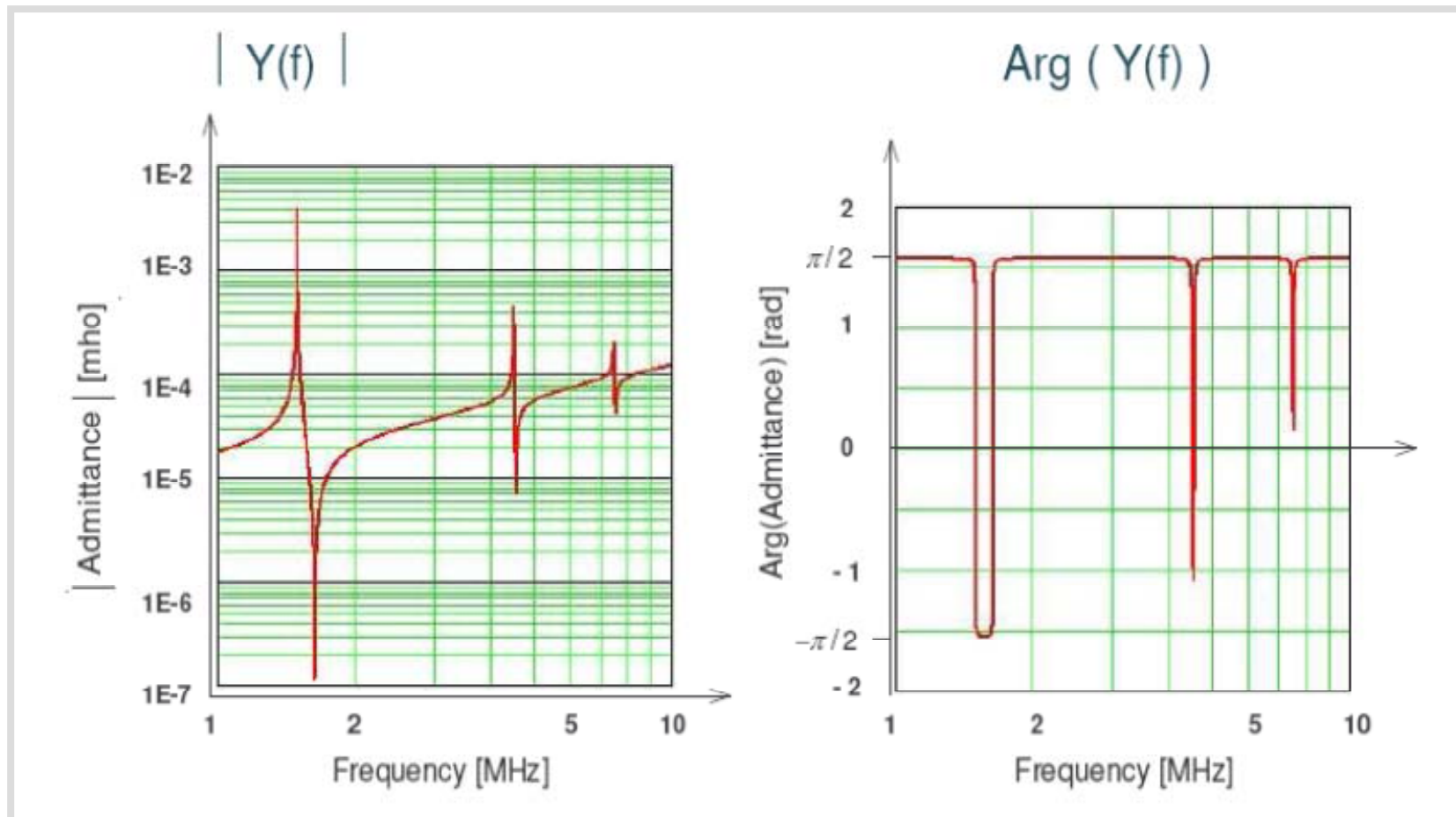


Third Overtone
Thickness Shear

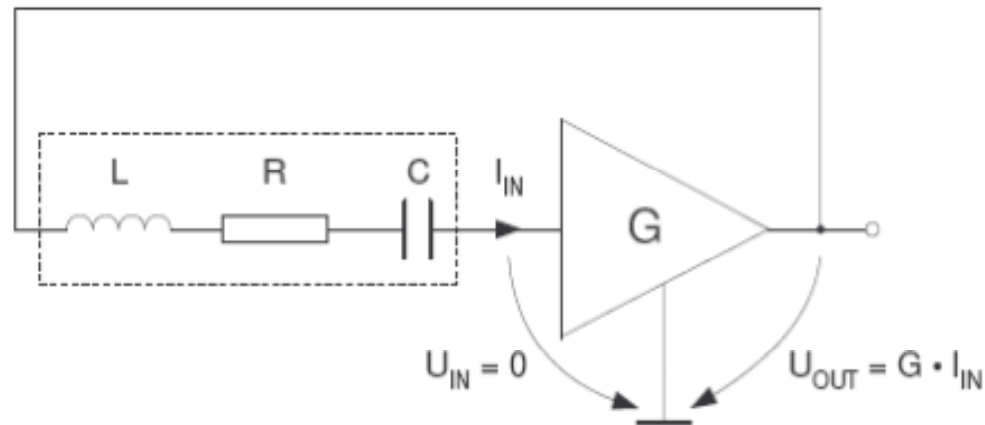
ACOUSTIC WAVE SENSORS



ACOUSTIC WAVE SENSORS



ACOUSTIC WAVE SENSORS



$$\text{Open Loop Gain: } H(\omega) = G \cdot Y(\omega) = \frac{G}{j \cdot \omega \cdot L + R + \frac{1}{j \cdot \omega \cdot C}}$$

$$\text{If } G = \frac{1}{R} \text{ and } \omega = \omega_0 = \frac{1}{\sqrt{L \cdot C}} \text{ then } H(\omega = \omega_0) = 1$$

$$f_0 = \frac{\omega_0}{2 \cdot \pi} = \text{resonance frequency}$$

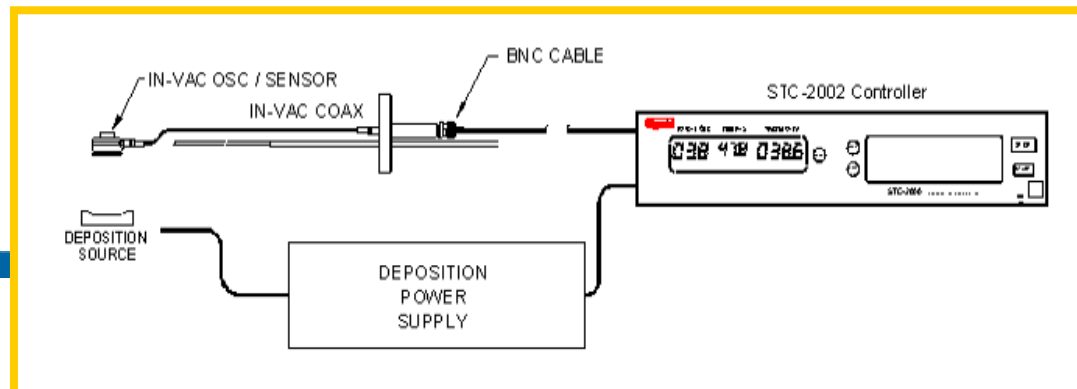
ACOUSTIC WAVE SENSORS

THIN FILM THICKNESS MEASUREMENT (TSM)



Specifications

- Crystal Sensor: Industry standard 6 MHz Max
- Temperature: 150°C In-Vac Oscillator Sensor
- Sensor Mounting: Rear of body, #4-40 Tapped
- Materials: 304 SS, Alumina, Teflon
- Crystal: Quartz with Gold Electrodes
- Water Temp: 50°C
- Connection: Microdot Miniature



Acoustic Wave Sensors

Properties of piezoelectric thin film

1. value of electromechanical coupling;
2. good adhesion to substrate;
3. resistance to environmental effects (e.g., humidity, temperature);
4. VLSI process compatible (e.g., deposition methods and etching);
5. temperature and acceleration sensitivity;
6. cost effectiveness.

Acoustic Wave Sensors

Properties of piezoelectric thin film

SiO₂ (Quartz)

- Natural
- Synthetic

ZnO (Zinc Oxide)

- High piezoelectric coupling
- stability
 - Magnetron sputtering

AlN (Aluminium Nitride)

- High acoustic velocity (GHz region)
- Reactive Magnetron sputtering

Acoustic Wave Sensors

Properties of piezoelectric thin film

AlN (Aluminium Nitride)

– Reactive Magnetron sputtering

Atmospheric gas	Ar + N ₂ (1:1) or N ₂
Gas pressure	10^{-2} – 3×10^{-3} Torr
Substrate temperature	50–500°C
Target material	99.6–99.99% pure Al
Target size	diameter 100 mm, thickness 6 (mm)
Target-substrate spacing	40 mm
Input RF power	100–200 W
Film-thickness range	1–7 μm
Sputtering rate	0.2–0.8 ($\mu\text{m}/\text{h}$)

Acoustic Wave Sensors

Properties of piezoelectric thin film

$\text{Pb}(\text{Zr}, \text{Ti})\text{O}_3$ (PZT)

- Highest Piezo coupling factor (10 times higher)
- Large pyroelectric response (infra red sensitive)
 - E-beam evaporation
 - RF sputtering
 - Sol-Gel
 - Laser ablation
 -

Acoustic Wave Sensors

Properties of piezoelectric thin film

TABLE 2 Application Summary of Three Major Piezo-Films ZnO, AlN, and PZT

Applications	Piezoelectric Materials			
	ZnO	AlN	PZT	Others
Pressure sensors	✓			✓
Gas sensors				✓
Bulk acoustic resonators	✓	✓		
Plate mode sensors	✓			✓
Accelerometers	✓			✓
TV VIF filters	✓		✓	
SAW devices	✓	✓	✓	
Actuator/translator	✓		✓	

ACOUSTIC WAVE SENSORS

ULTRASONIC SENSORS

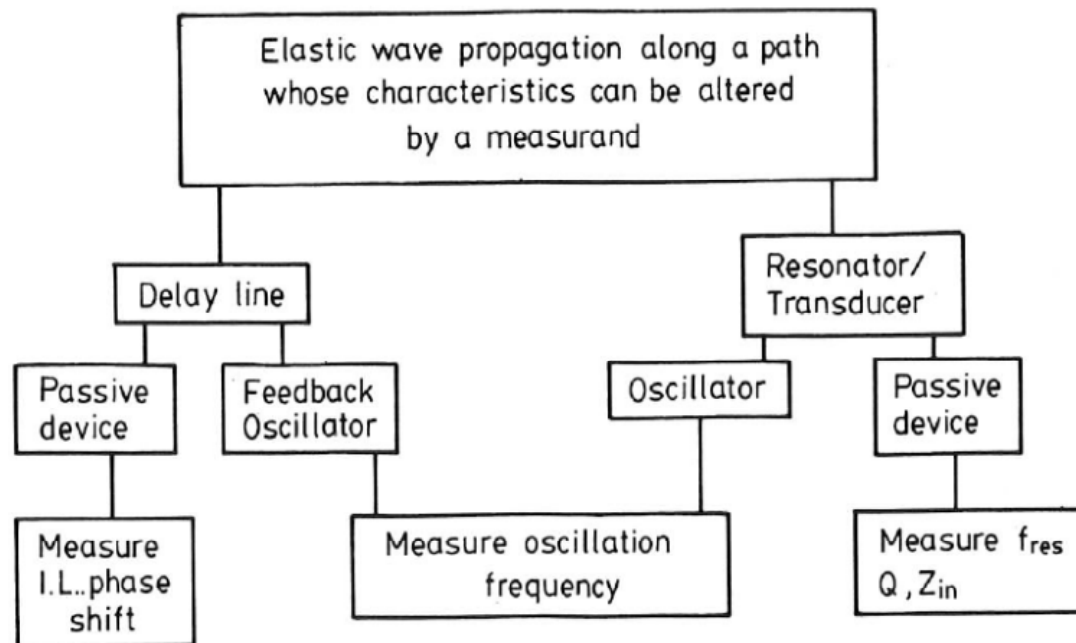


Fig. 6 Measurement options for ultrasonic resonators and delay lines.

ACOUSTIC WAVE SENSORS

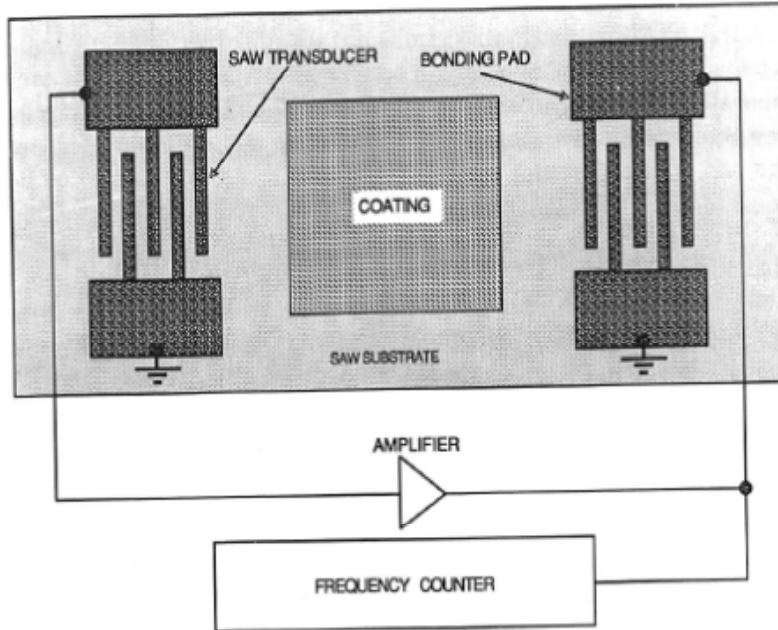


Fig. 17 Schematic of SAW gas sensor concept.

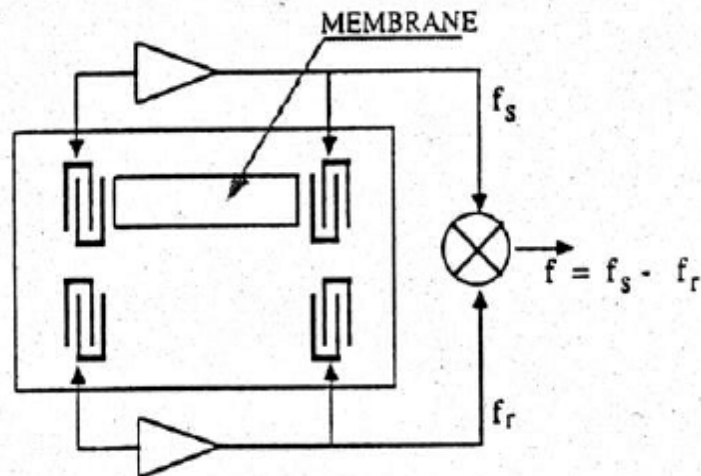
Gas sensor SAW

Coating absorb mesurand

Problem! temperature
dependence

ACOUSTIC WAVE SENSORS

SAW sensor in a twin sensor configuration



(b)

Figure 17: Differential structure for phase shift detection technique (a) and frequency shift detection technique (b).

ACOUSTIC WAVE SENSORS

WORKING PRINCIPLE SAW

Surface acoustic wave (SAW)

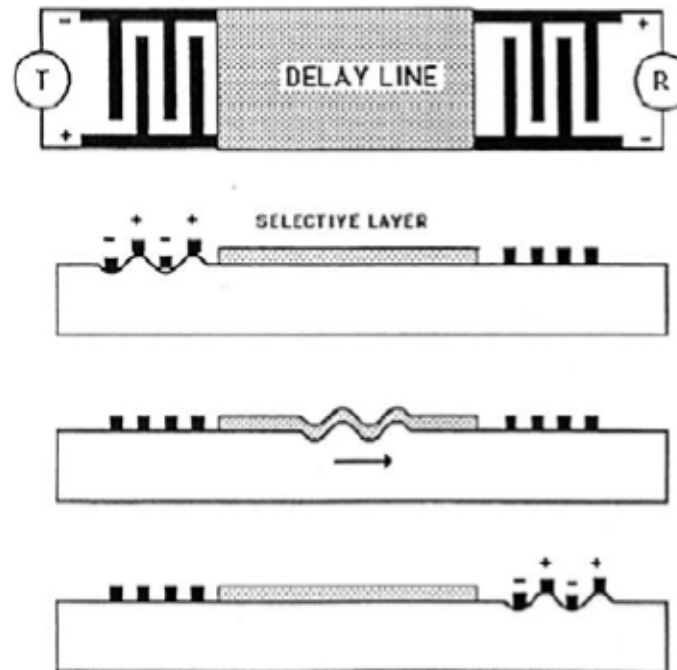


Figure 3-12. Schematic diagram of a SAW sensor with transmitter T, receiver R, and the chemically selective layer deposited on the delay line.

Acoustic Wave Sensors

SAW in a oscillator circuit

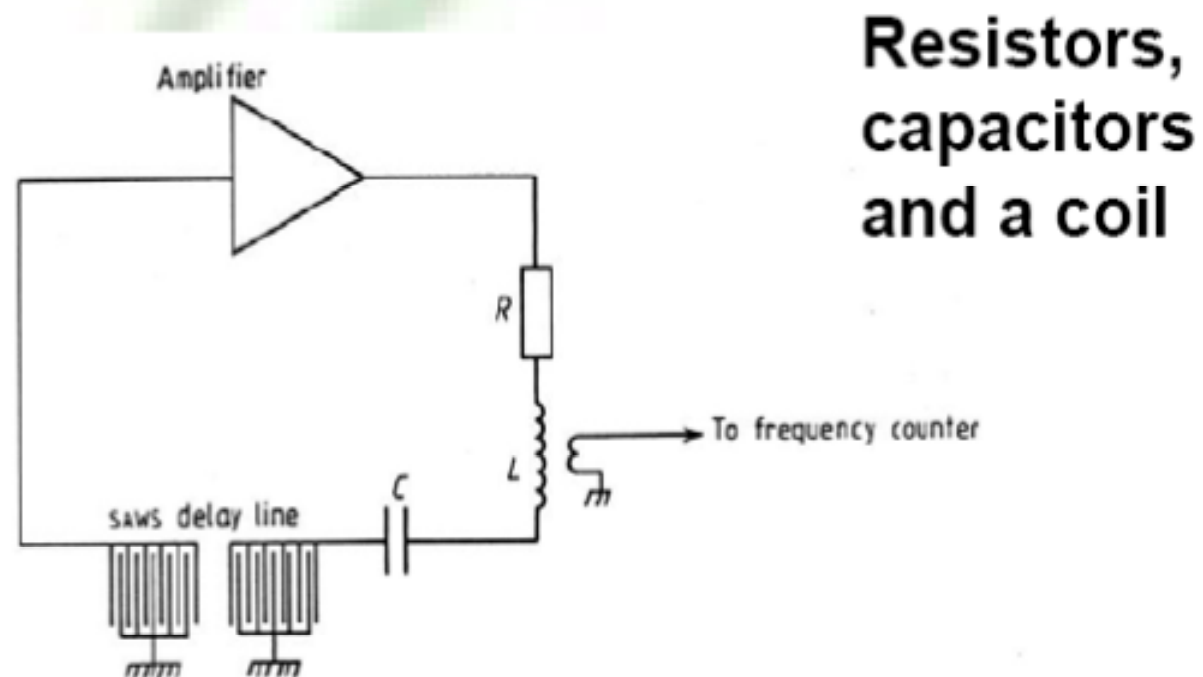


Figure 13.2 Delay line oscillator (schematic representation).

ACOUSTIC WAVE SENSORS

TABLE 4 Summary of Various SAW Chemical Sensors

Measurand	Chemical Interface	SAW Substrate	Reference
Organic vapor	Polymer film	Quartz	81–83
SO ₂	TEA ^a	Lithium niobate	84
H ₂	Pd	Lithium niobate, silicon	85, 86
NH ₃	Pt	Quartz	87
H ₂ S	WO ₃	Lithium niobate	88
Water vapor	Hygroscopic	Lithium niobate	89, 90
NO ₂	PC ^b	Lithium niobate, quartz	91–93
NO ₂ , NH ₃ , CO, SO ₂ , CH ₄	PC ^b	Lithium niobate	94
Vapors of explosives, drugs	Polymer films	Quartz	95
CO ₂ , Methane	C ^c	Lithium niobate	96

^a TEA = Triethanolamine.

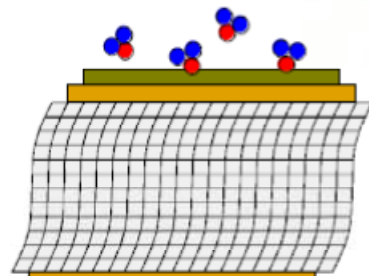
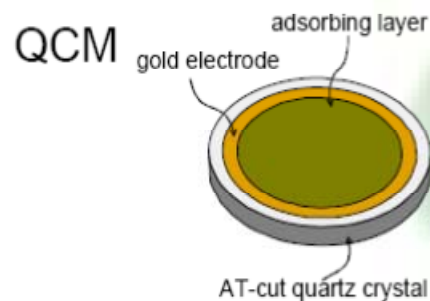
^b PC = Phthalocyanine.

^c C = No chemical interface used. Detection based on changes in thermal conductivity produced by the gas.

Acoustic Wave Sensors

Comparison between TSM and SAW

Mass sensitive Resonator sensors



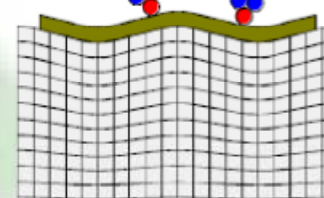
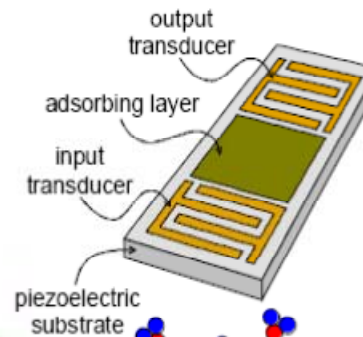
Thickness shear mode:

Typical resonance frequency: 5-30 MHz

For AT cut quartz:

$$\Delta f = -2.3 \times 10^6 f_0^2 \frac{\Delta m}{A}$$

SAW



Surface (Rayleigh) wave:

Typical resonance

frequency: 100-500 MHz

For YX cut quartz:

$$\Delta f = -1.3 \times 10^6 f_0^2 \frac{\Delta m}{A}$$

QCM at 10 MHz
and SAW at 100 MHz:

$$\frac{\Delta F_{SAW}}{\Delta F_{QCM}} = \frac{1.3 \times 10^6 100^2}{2.3 \times 10^6 10^2} \approx 60$$

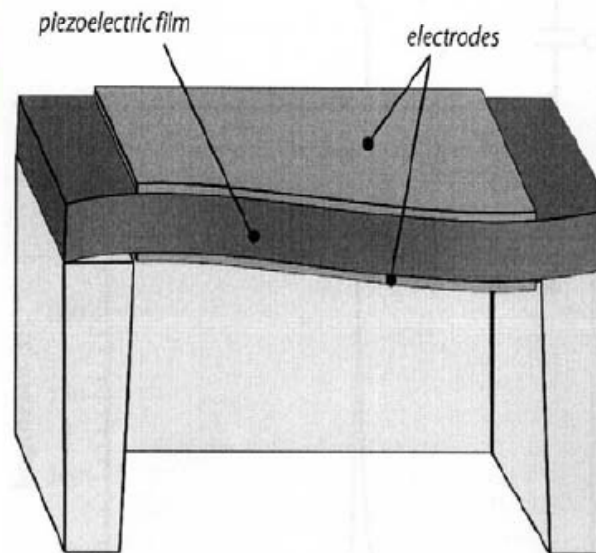
Acoustic Wave Sensors

Example of FPW

AlN based bulk acoustic resonators

Uppsala
University,
Sweden and
S-SENCE

AlN sputter
deposited



Bulk
resonating
thin film
(2 μ m)
device

J. Bjurström, D. Rosén, I. Katardjiev, V.M. Yanchev, I. Petrov, (Sweden)
IEEE Trans. Ultrasonics ferroelectr. And freq. Control, 2004

Uppsala, spring 2005, A. Lloyd Spetz

S-SENCE
Linköping University



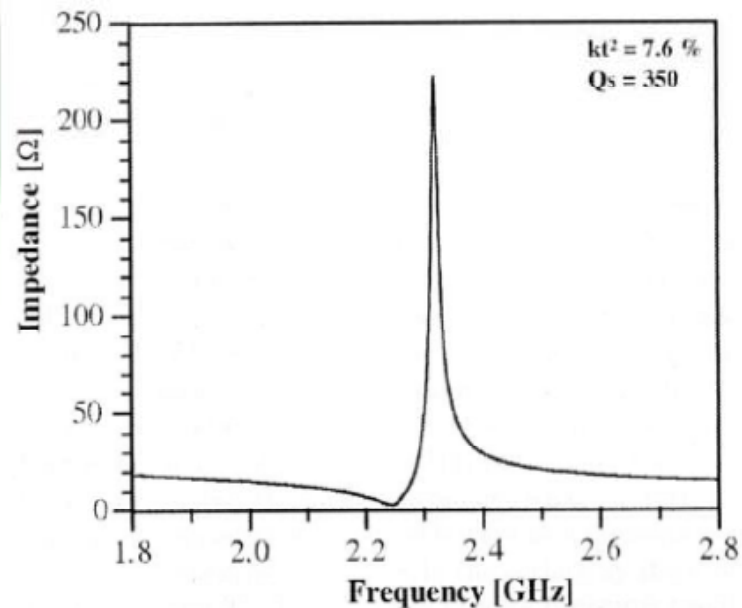
Acoustic Wave Sensors

Example of FPW

AlN based bulk acoustic resonators

Typical
resonance
frequency
of ~ 2GHz

Potential of
very high
sensitivity



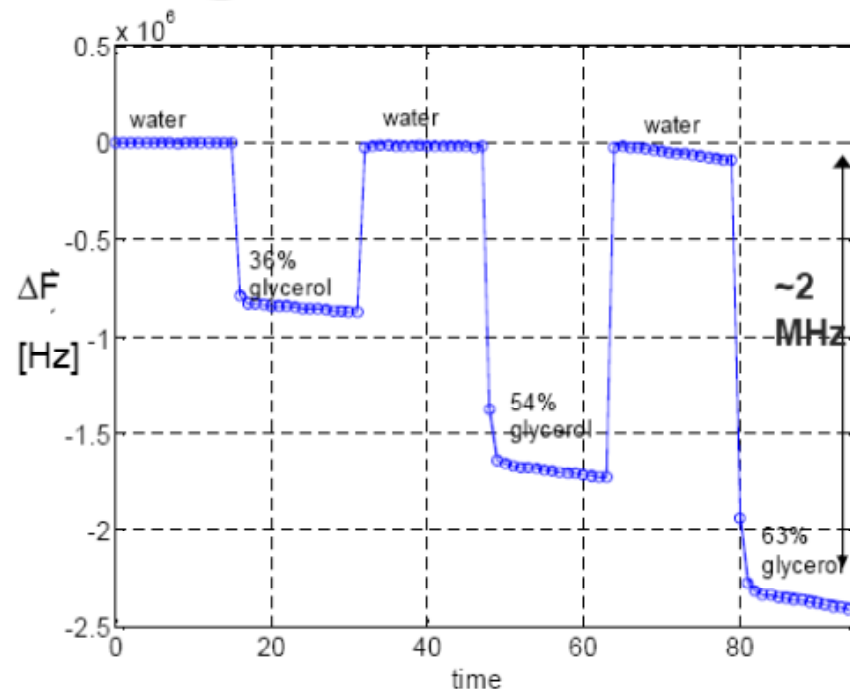
J. Bjurström, D. Rosén, I. Katardjiev, V.M. Yanchev, I. Petrov,
J. Bjurström et al., IEEE Trans. Ultrason. Ferroelectr. And freq. Control, 2004
Uppsala, spring 2005, A. Lloyd Spetz



Acoustic Wave Sensors

Example of FPW

AlN based bulk acoustic resonators as gas and biosensors

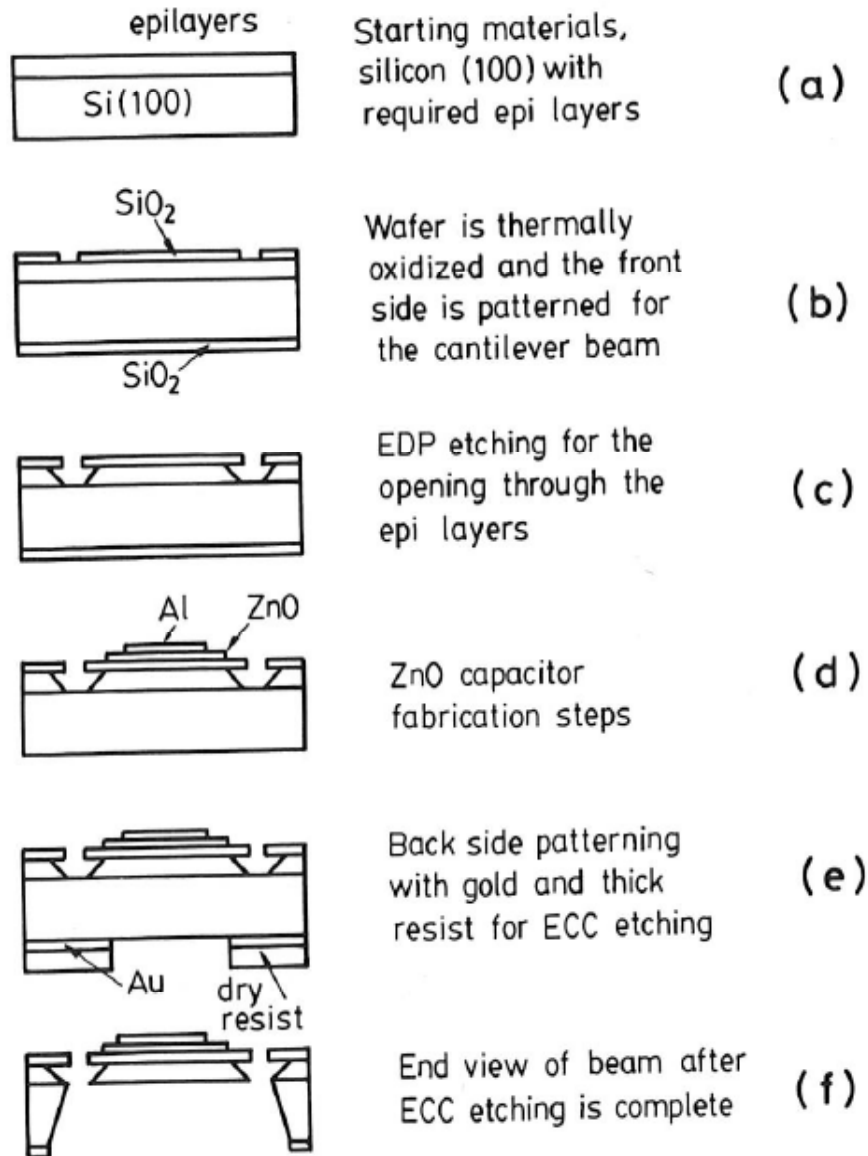


Response to different concentrations of glycerol in water

Gunilla Wingqvist, Uppsala University, Sweden
Uppsala, spring 2005, A. Lloyd Spetz

ACOUSTIC WAVE SENSORS

Processing of a Cantilever beam in silicon



ACOUSTIC WAVE SENSORS

Monolithic
accelerometer
compatible with
standard
processing
technology

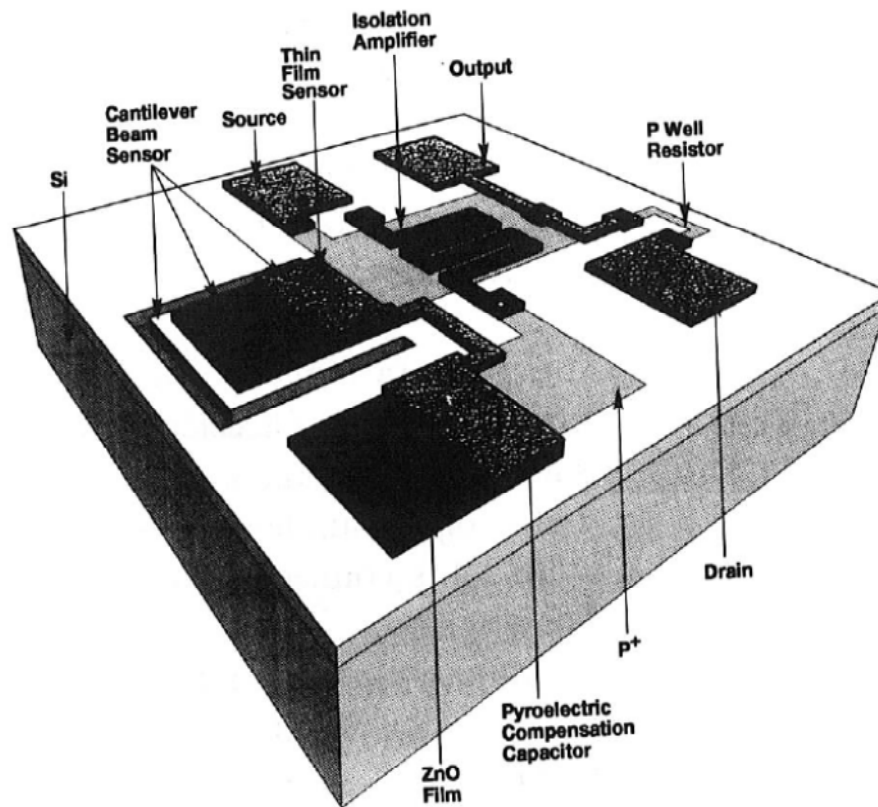
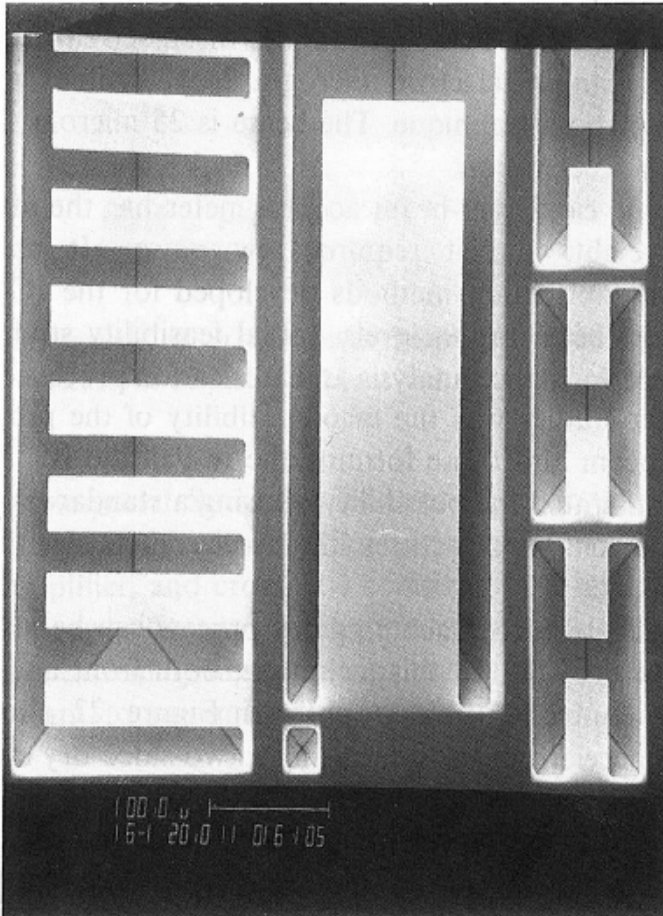


Fig. 18 Schematic of a silicon monolithic cantilever beam.

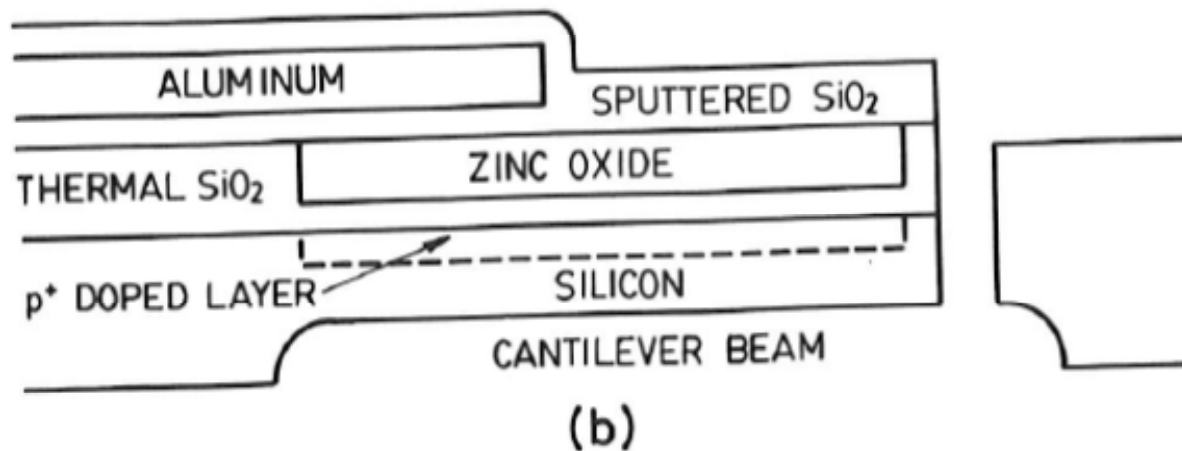
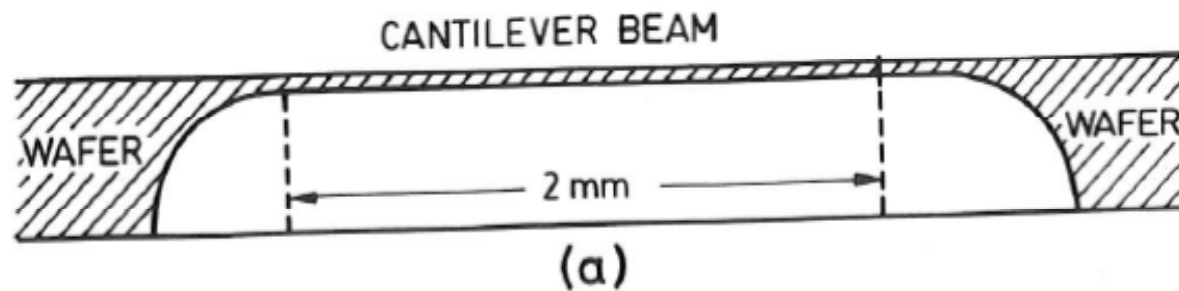
ACOUSTIC WAVE SENSORS



Test structure to investigate etching properties and constraints in fabrication of silicon dioxide cantilever beams

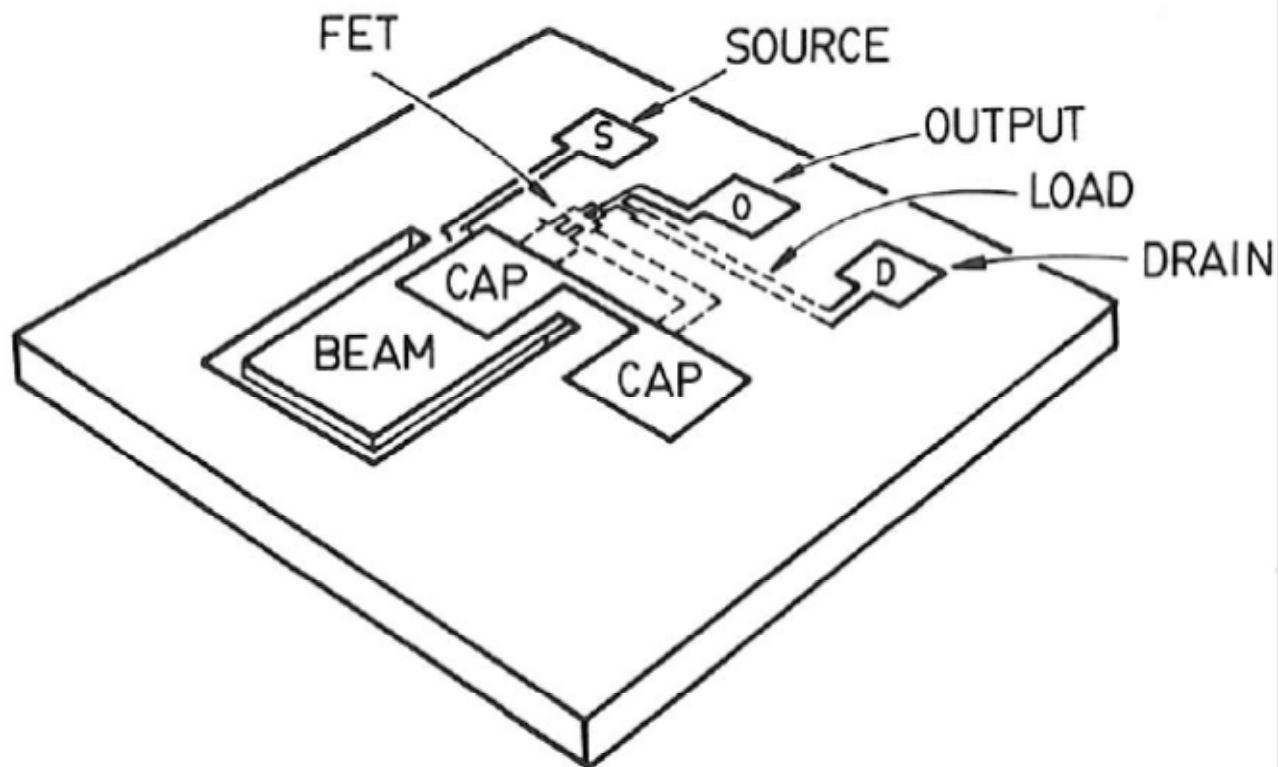
ACOUSTIC WAVE SENSORS

CROSS SECTION OF THE CANTILEVER-BEAM ACCELEROMETER



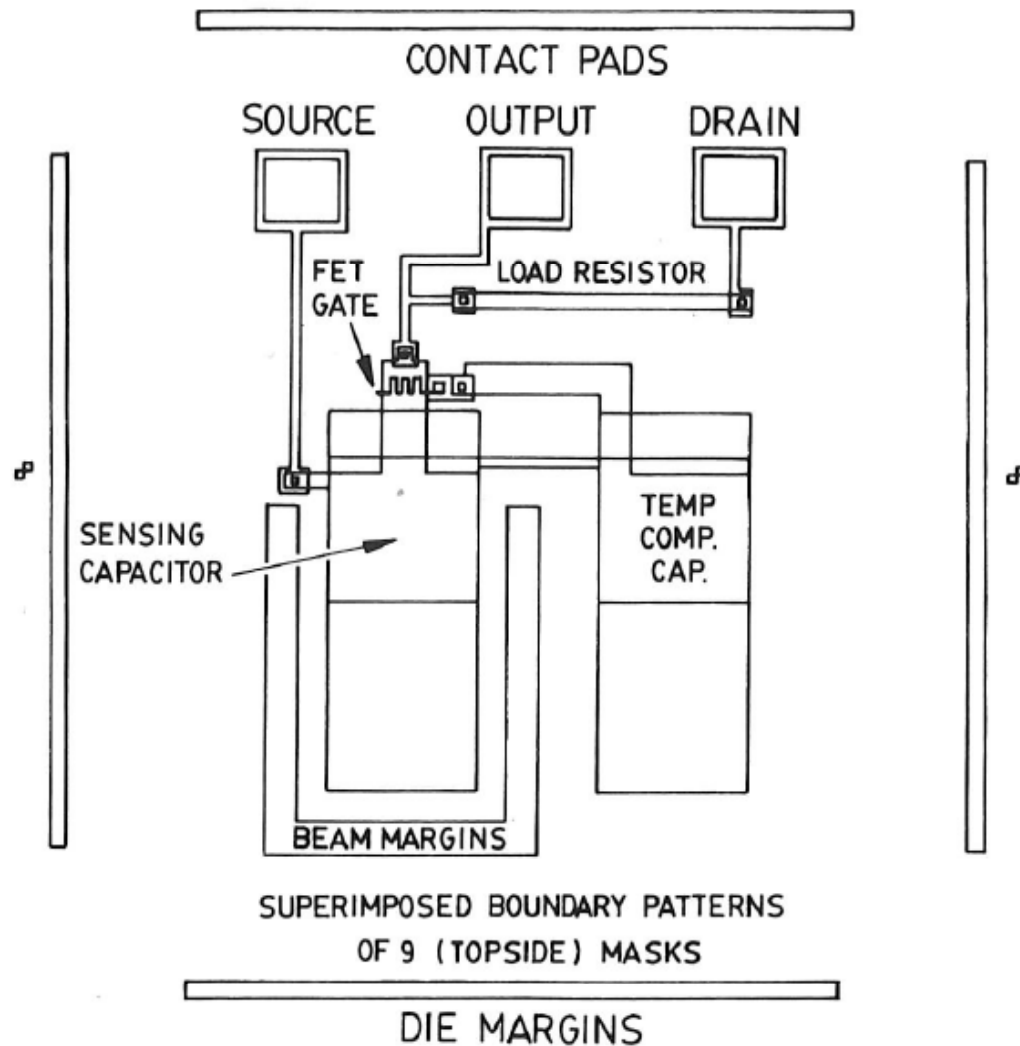
ACOUSTIC WAVE SENSORS

SCHEMATIC LAYOUT



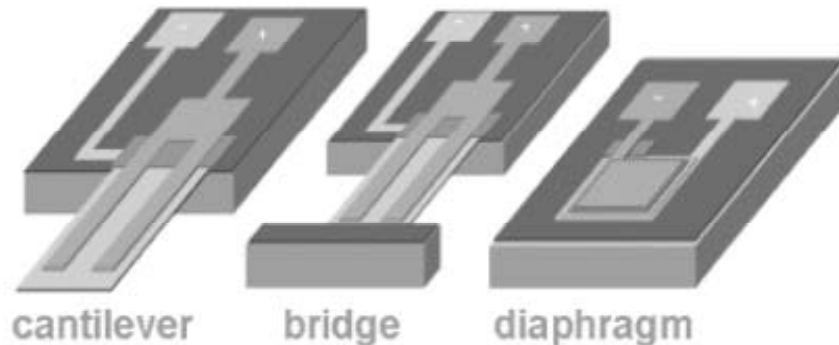
ACOUSTIC WAVE SENSORS

Top view, indicating
the use of 9 masks

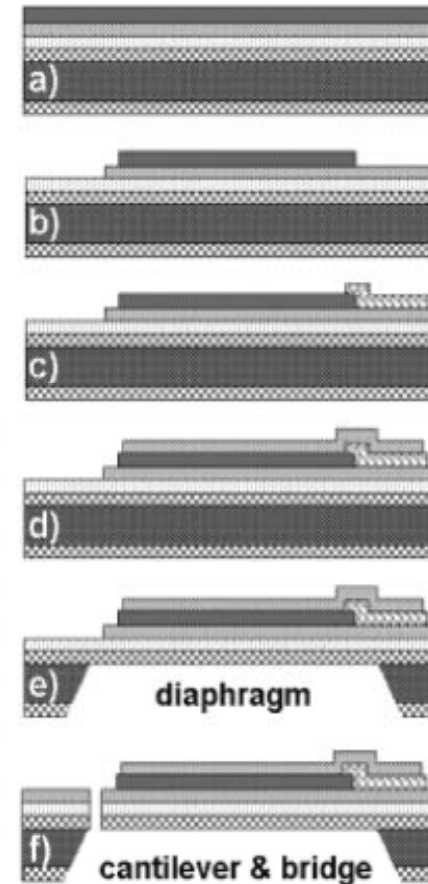


ACOUSTIC WAVE SENSORS

Piezoelectric Microtransducers

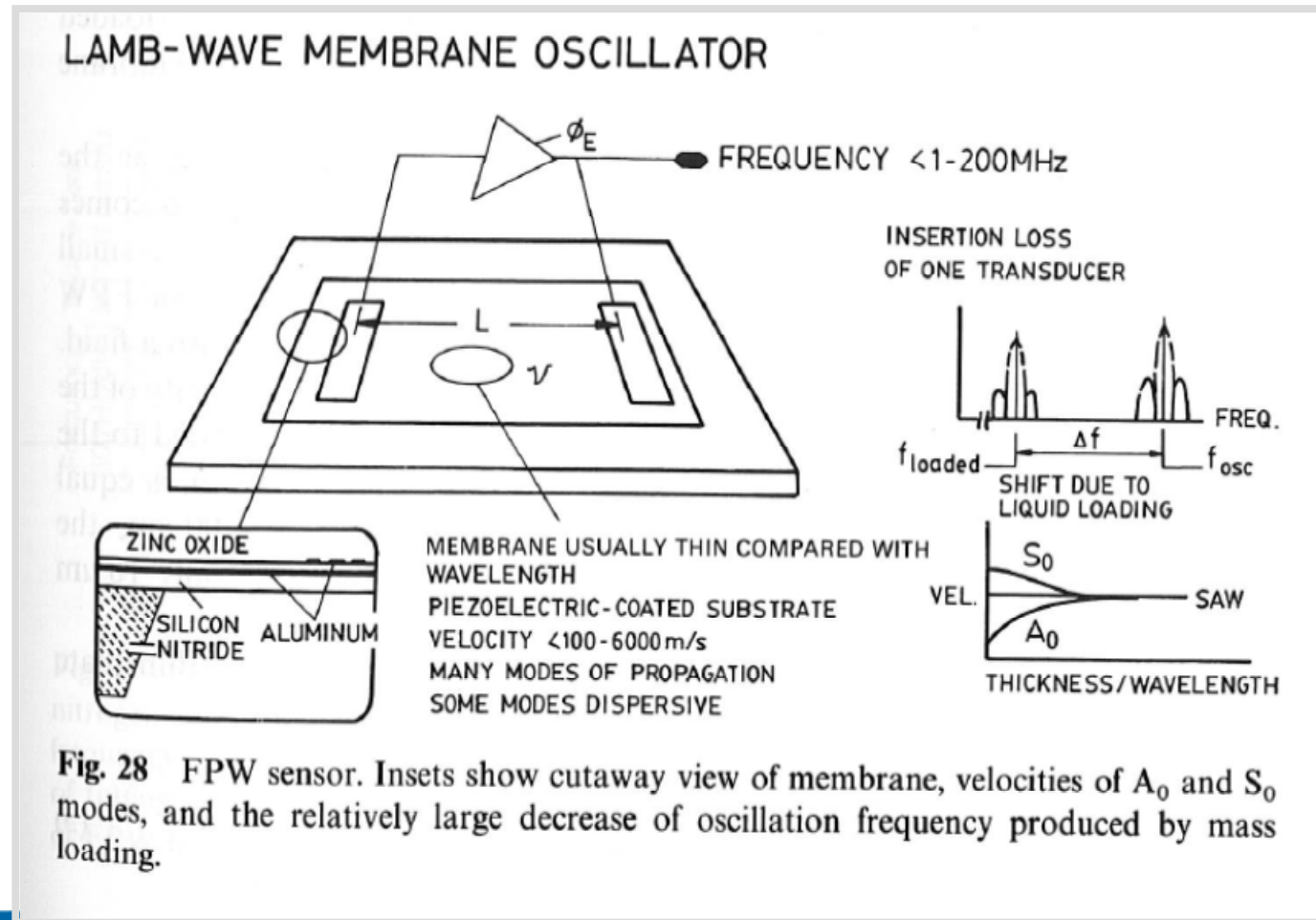


Pattern	Layer Materials	Layer Thickness (nm)
	Sensing polymer	
	Top electrode	100
	PZT [$\text{Pb}(\text{Zr}_{0.52}\text{Ti}_{0.48})\text{O}_3$]	500
	Polyimide (ILD - Insulator)	1200
	Bottom electrode (Pt/Ta)	150/20
	Silicon dioxide	300
	Silicon nitride	1200
	Silicon (100-oriented)	475 micron



Acoustic Wave Sensors

FPW Sensor



ACOUSTIC WAVE SENSORS CANTILEVER-RESONATOR

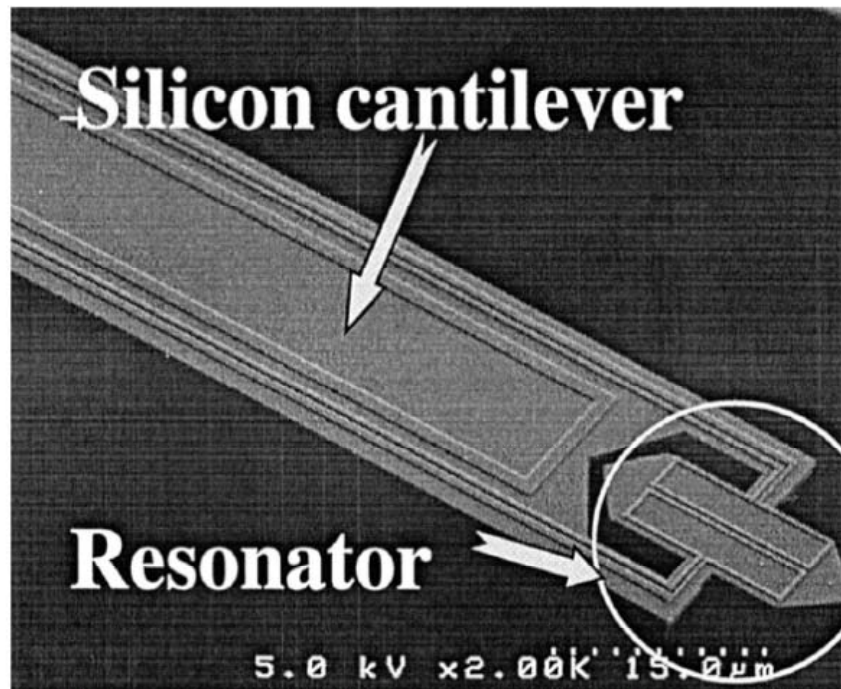


Fig. 8. A close-up view of the torsional resonator.

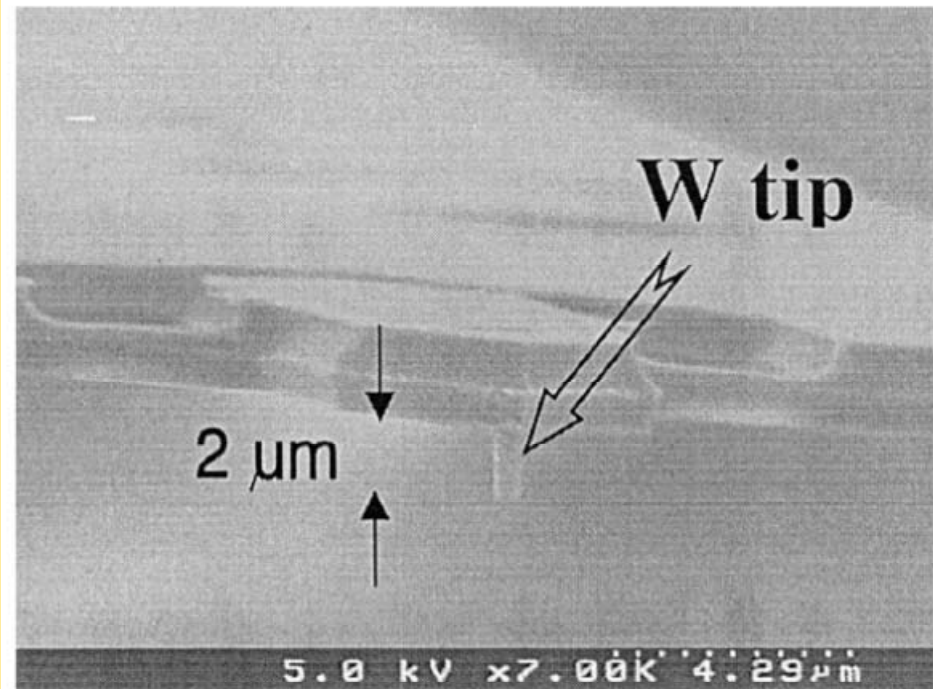


Fig. 9. After release, fabricated tip by FIB.

ACOUSTIC WAVE SENSORS

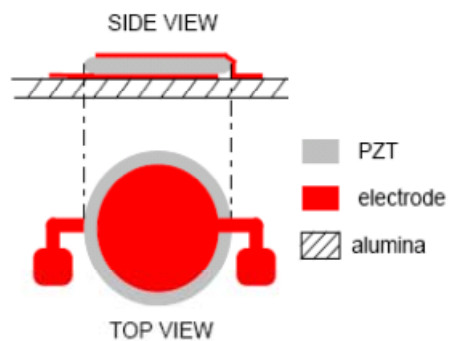


Fig. 1. Structure of a RPL.

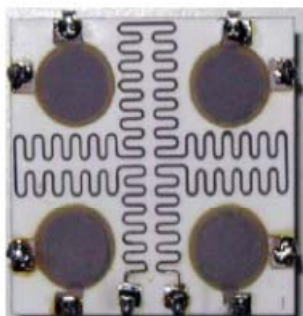


Fig. 2. RPL array.

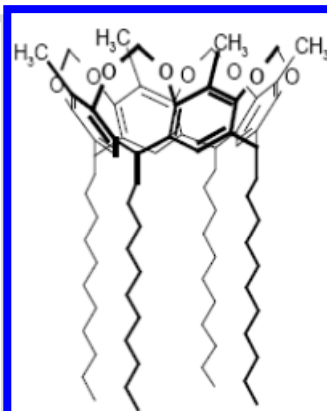


Fig. 3. Me-Cav.

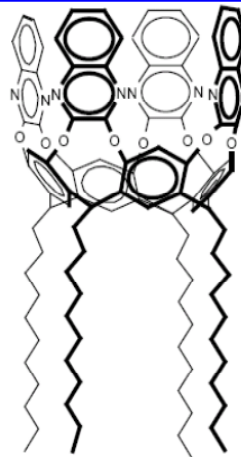


Fig. 4. Qx-Cav.

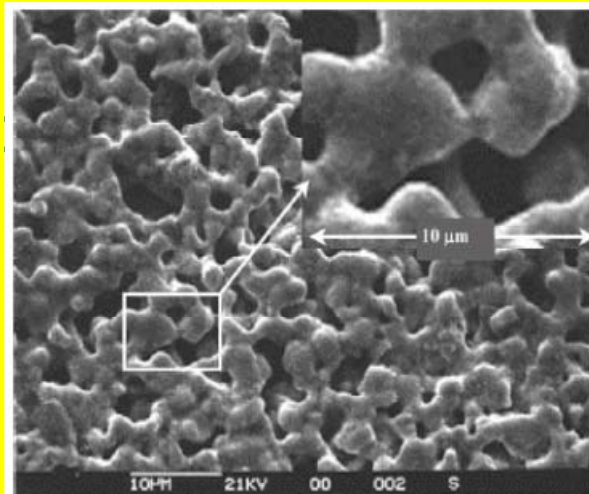


Fig. 5. SEM photograph of the RPL surface.

ACOUSTIC WAVE SENSORS

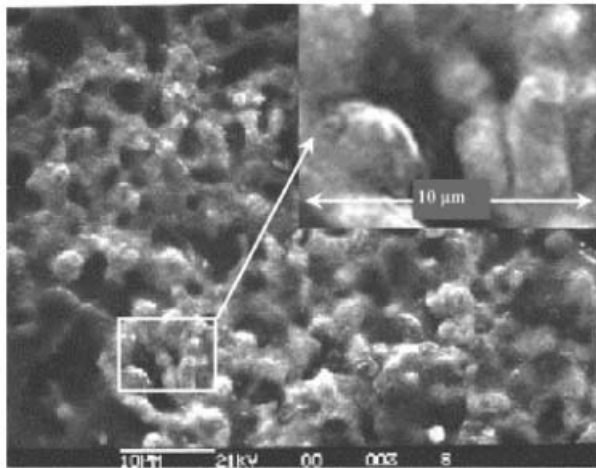


Fig. 6. SEM photograph of the RPL surface sensitized with 40 µl of Me-Cav by casting deposition.

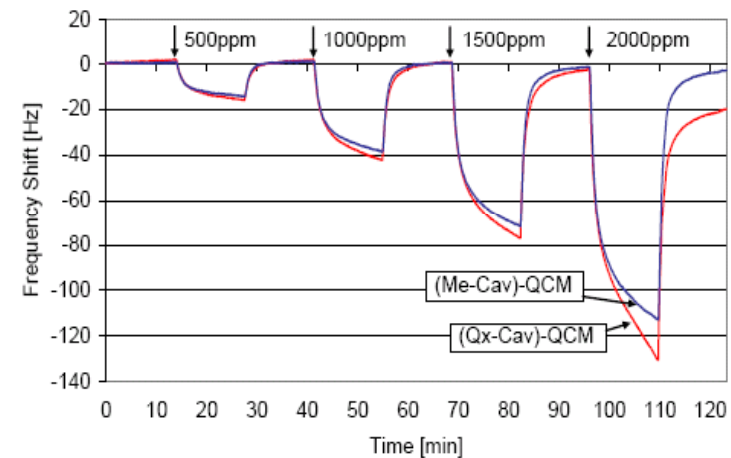


Fig. 10. (Me-Cav)-QCM and (Qx-Cav)-QCM responses to stepping concentrations of toluene at room temperature.

Surface after deposition of
cavitands

Measuring concentration of toluene